



US-Africa Initiative Workshop

APS March Meeting - Sunday, March 14, 2021

Sponsored by the APS Innovation Fund

[Omololu AKIN-OJO]

ICTP East African Institute for
Fundamental Research (EAI FR), Rwanda



Major interest is in “Methods Development”:
**Accurate results “without too much
computation”** includes force field development,
Improved Tight Binding /Semi-Empirical methods
from ab initio data and now, Machine Learning

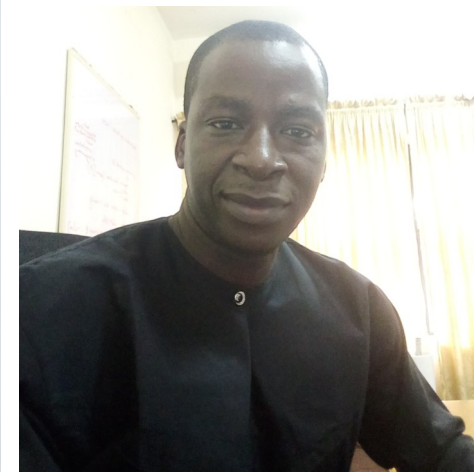
***Secondary interest is in the application of these
methods to technologically important systems and,
possibly biomedical applications***



Ezekiel Oyeniya, PhD
Candidate Univ. Ibadan:
EOMCCSD -> ZINDO/S



Damilare Babatunde,
MSc Candidate Univ.
Ibadan: Water Splitting



Akorede Joledo, PhD
Candidate Univ. Ibadan:
Water Splitting



Firas Shuaib, MSc
Graduate, Univ. Rwanda
ML in Superconductivity



Sosthene Irambona, PhD
Candidate Univ. Rwanda
DFT+U



Ayoola Adeolu, PhD
Candidate Univ. Ibadan:
Battery Research

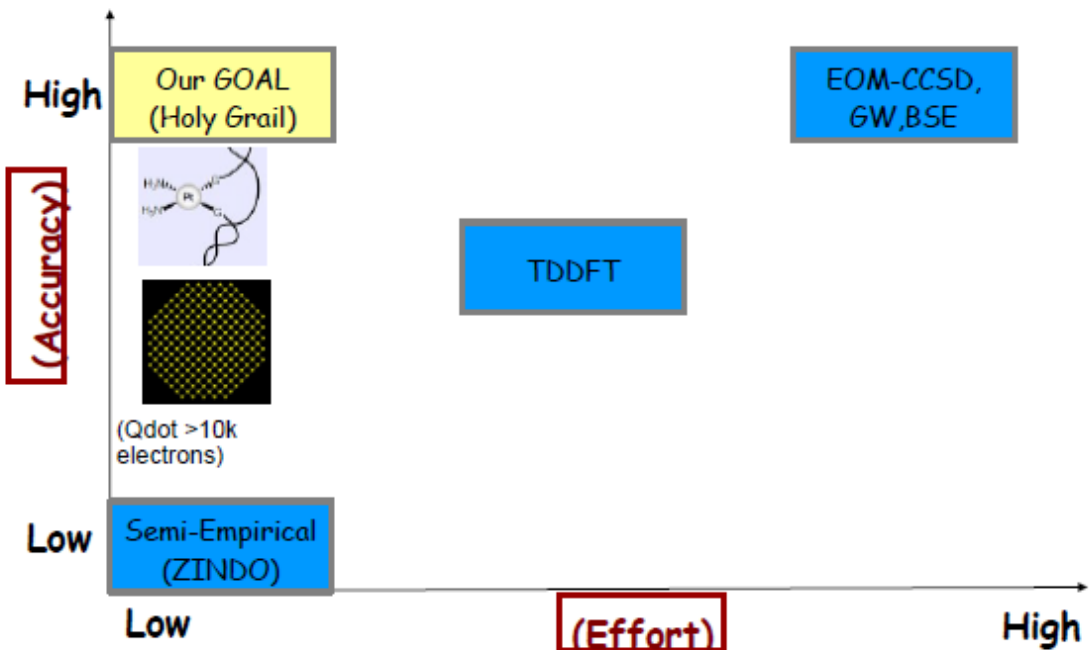
[Research Efforts and Collaborations in Akin-Ojo Research Group at EAI FR]

- Excited States for large systems: Second-Principles methods giving near-EOM-CCSD results at ZINDO/S cost
- Strongly Correlated Systems – DFT+U from atoms to compounds
- Predicting Superconducting Materials from Machine Learning
- Photocatalytic Water Splitting: Investigating SiNi, CNi, Si₂FeZn on MgO support for water splitting
- Battery research (beginning) using xTB and semi-empirical methods in MD
- Bulk Modulus of Osmium nanostructures
- Orbital-Free DFT (OFDFT): Search for Kinetic Energy Density Functional

[Example]

A second-principles approach for efficient determination of excitation energies and absorption spectra of quantum dots and large systems from ab initio data

... approximate practical methods of applying quantum mechanics ... [to explain] main features of complex atomic systems without too much computation - PAM Dirac, 1929

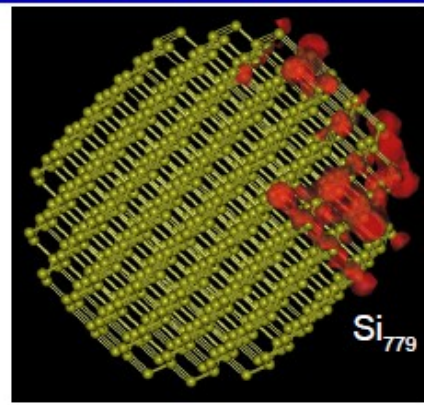


→ Fast + Accurate Prediction of Material Properties

EOM-CCSD → "oeINDO" : DIATOMIC

RESULTS: Mean Absolute Error (MAE): 0.2 eV

Si₇₇₉
 10,906 electrons
 3,116 valence electrons
 21-hr calculation on 1 processor



Methods	EOM-CCSD	TDDFT	CIS(D)
Si ₃			
oeINDO	0.22	0.17	0.39
ZINDO/S	0.91	0.98	0.74
Si ₄			
oeINDO	0.18	0.24	0.31
ZINDO/S	1.38	1.71	1.25
Si ₅			
oeINDO	0.09	0.04	0.16
ZINDO/S	1.47	1.52	1.39
Si ₁₉			
oeINDO	-	0.32	0.36
ZINDO/S	-	1.42	1.46
Si ₄₀			
oeINDO	-	0.12	0.03
ZINDO/S	-	0.68	0.80

